

This diagram shows a cross-sectional view of a semiconductor device. The substrate 2 consists of an n+ layer 10, a p layer 11, and an n+ layer 12. A trench 4 is formed in the substrate, with its bottom surface 12a. A gate oxide layer 6 is formed on the top surface of the substrate. A gate electrode 8 is formed on the gate oxide layer. A gate oxide layer 14 is formed on the top surface of the substrate. A gate electrode 13 is formed on the gate oxide layer. A gate oxide layer 18 is formed on the top surface of the substrate. A gate electrode 15 is formed on the gate oxide layer. A gate oxide layer 16 is formed on the top surface of the substrate. A gate electrode 17 is formed on the gate oxide layer. A gate oxide layer 18a is formed on the top surface of the substrate. A gate electrode 15a is formed on the gate oxide layer. A gate oxide layer 16a is formed on the top surface of the substrate. A gate electrode 17a is formed on the gate oxide layer. A gate oxide layer 18a is formed on the top surface of the substrate. A gate electrode 15a is formed on the gate oxide layer. A gate oxide layer 16a is formed on the top surface of the substrate. A gate electrode 17a is formed on the gate oxide layer.

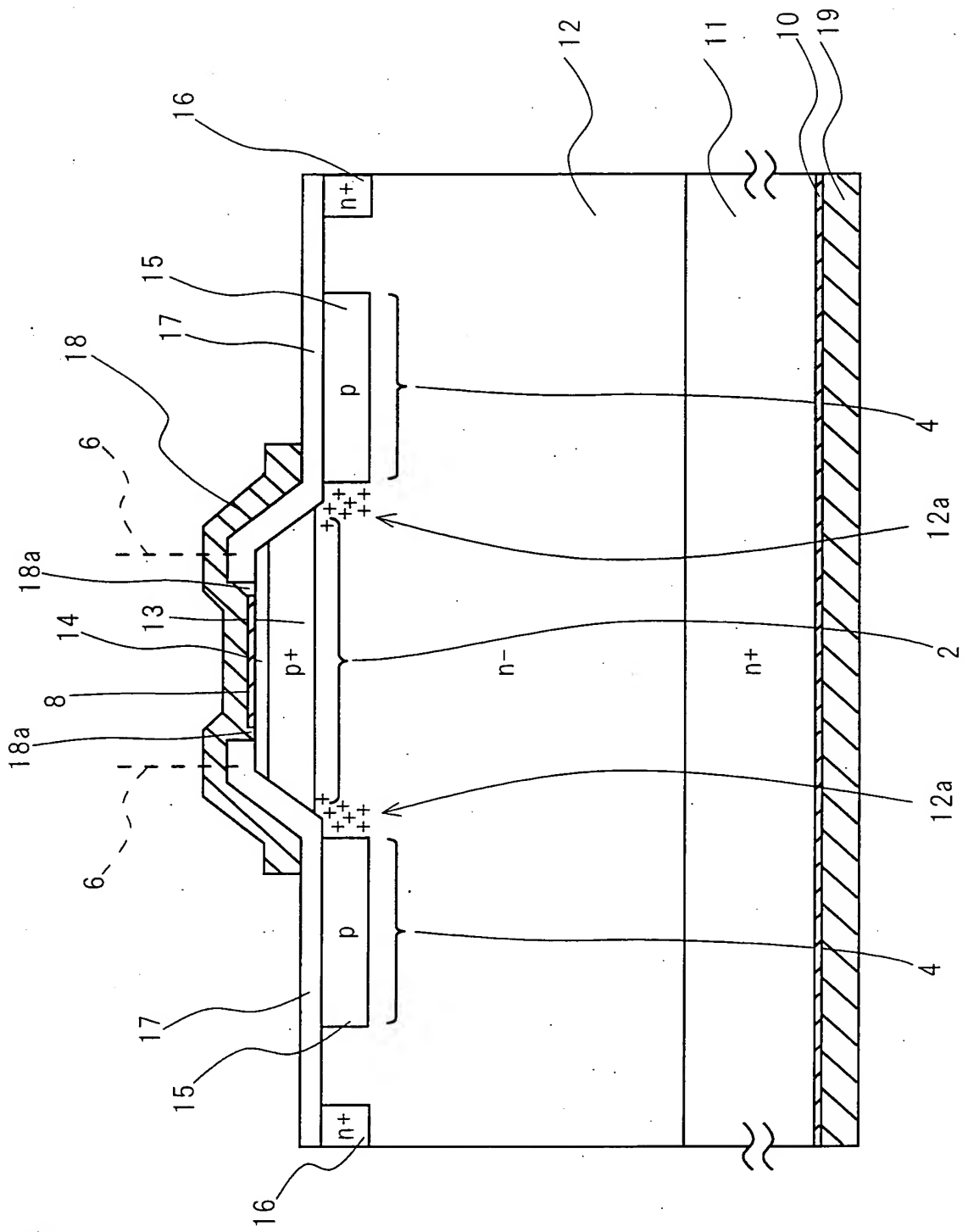


Fig. 2

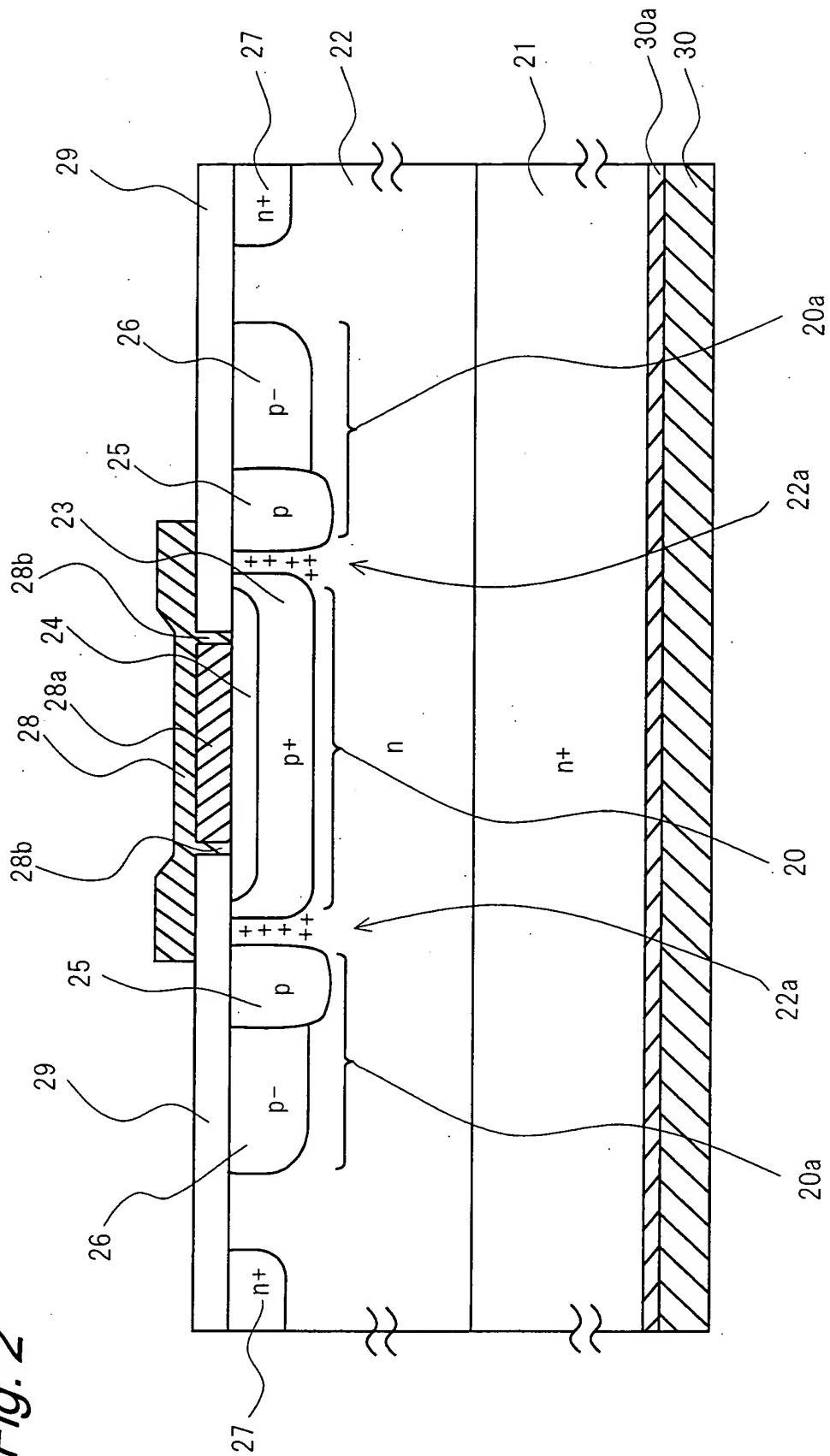


Fig. 3

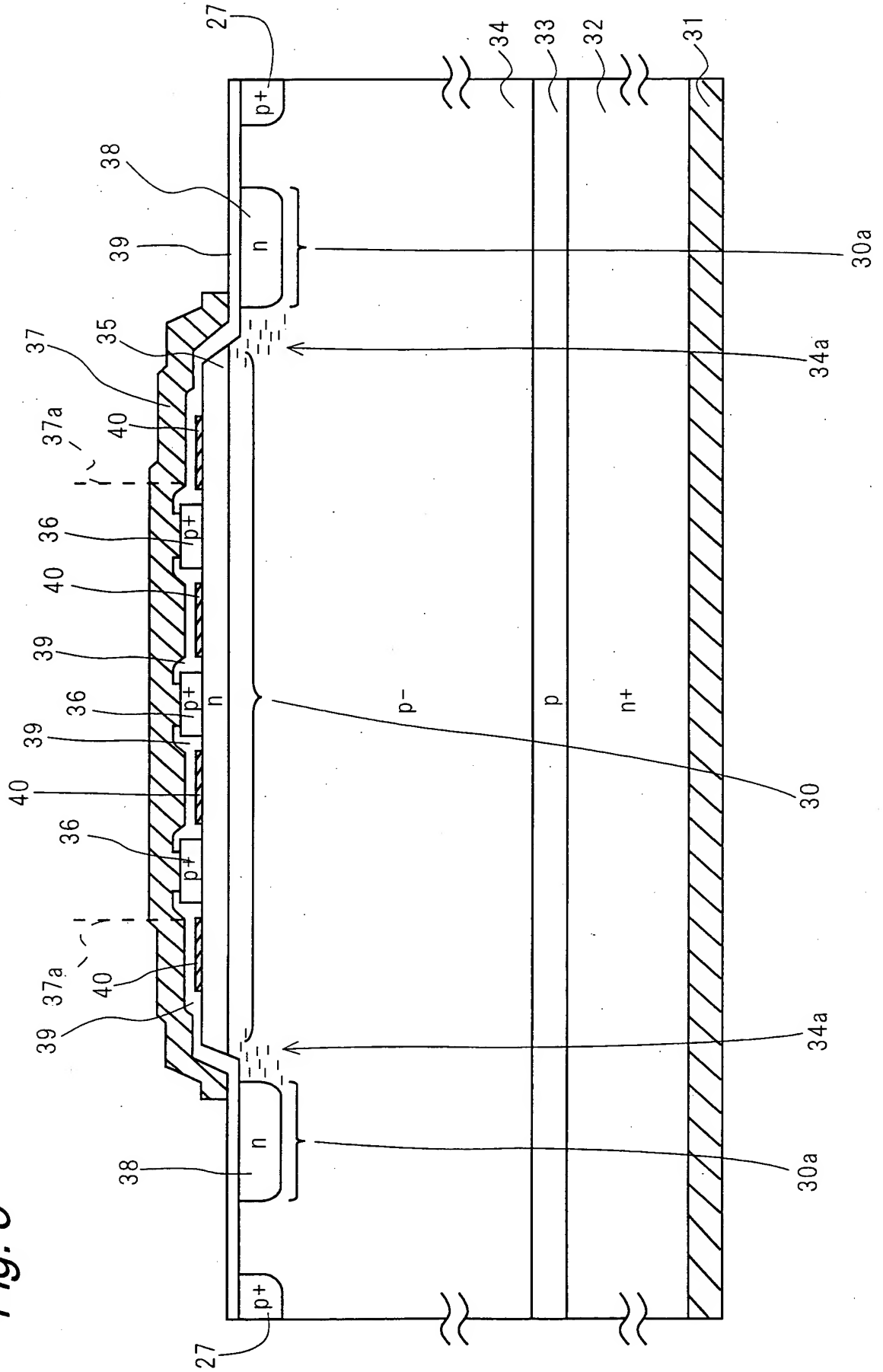


Fig. 4

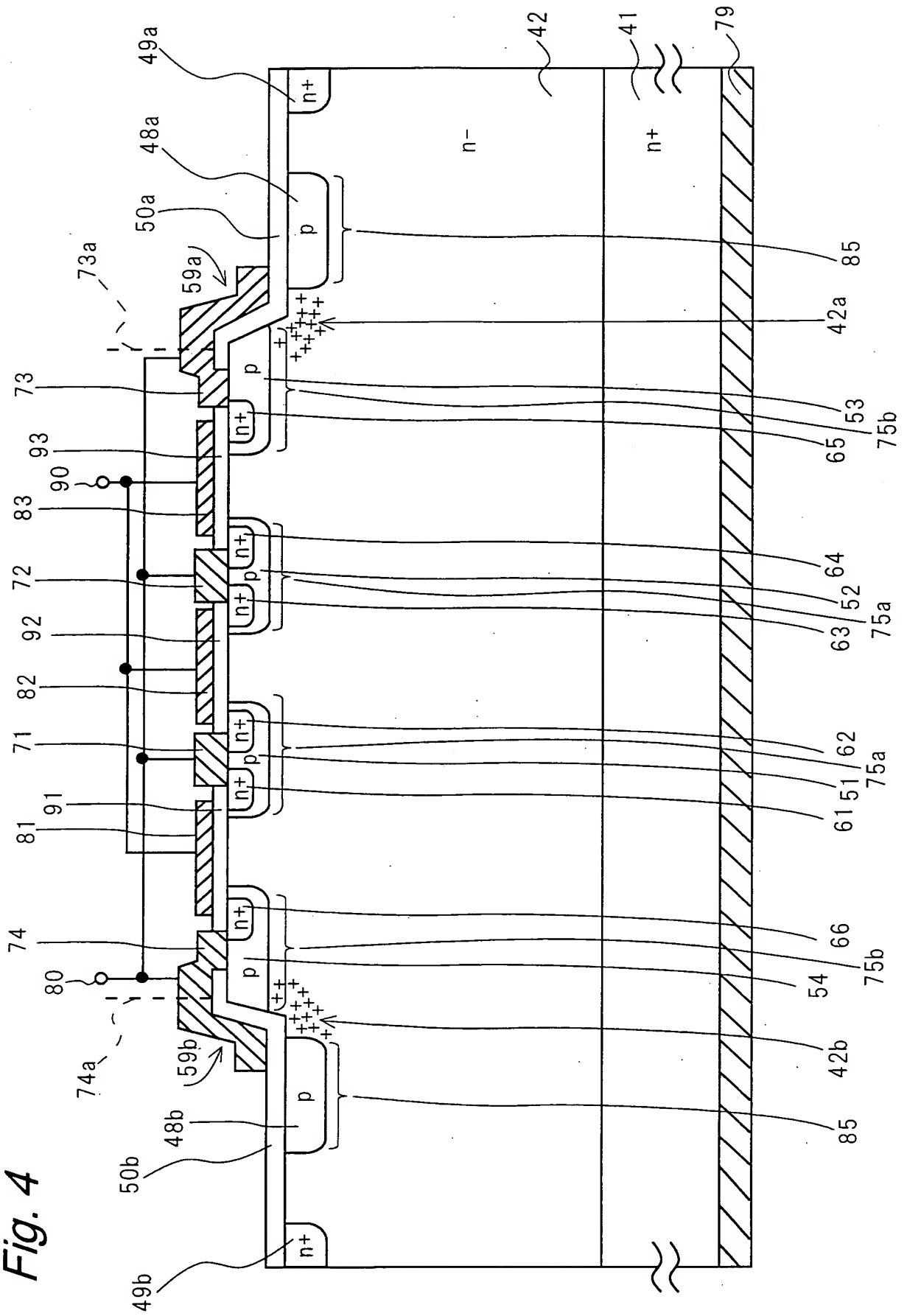


Fig. 5

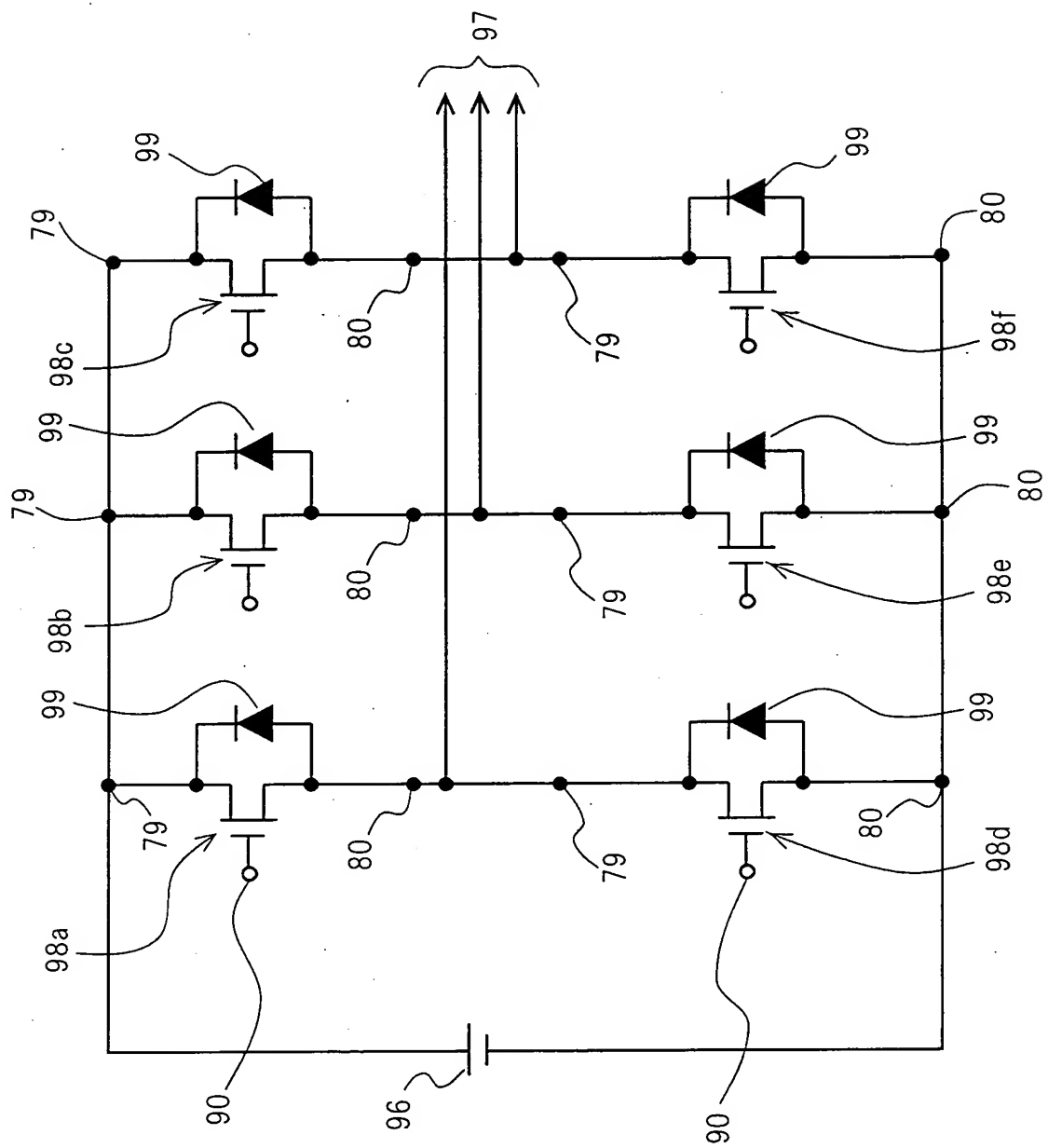


Fig. 6

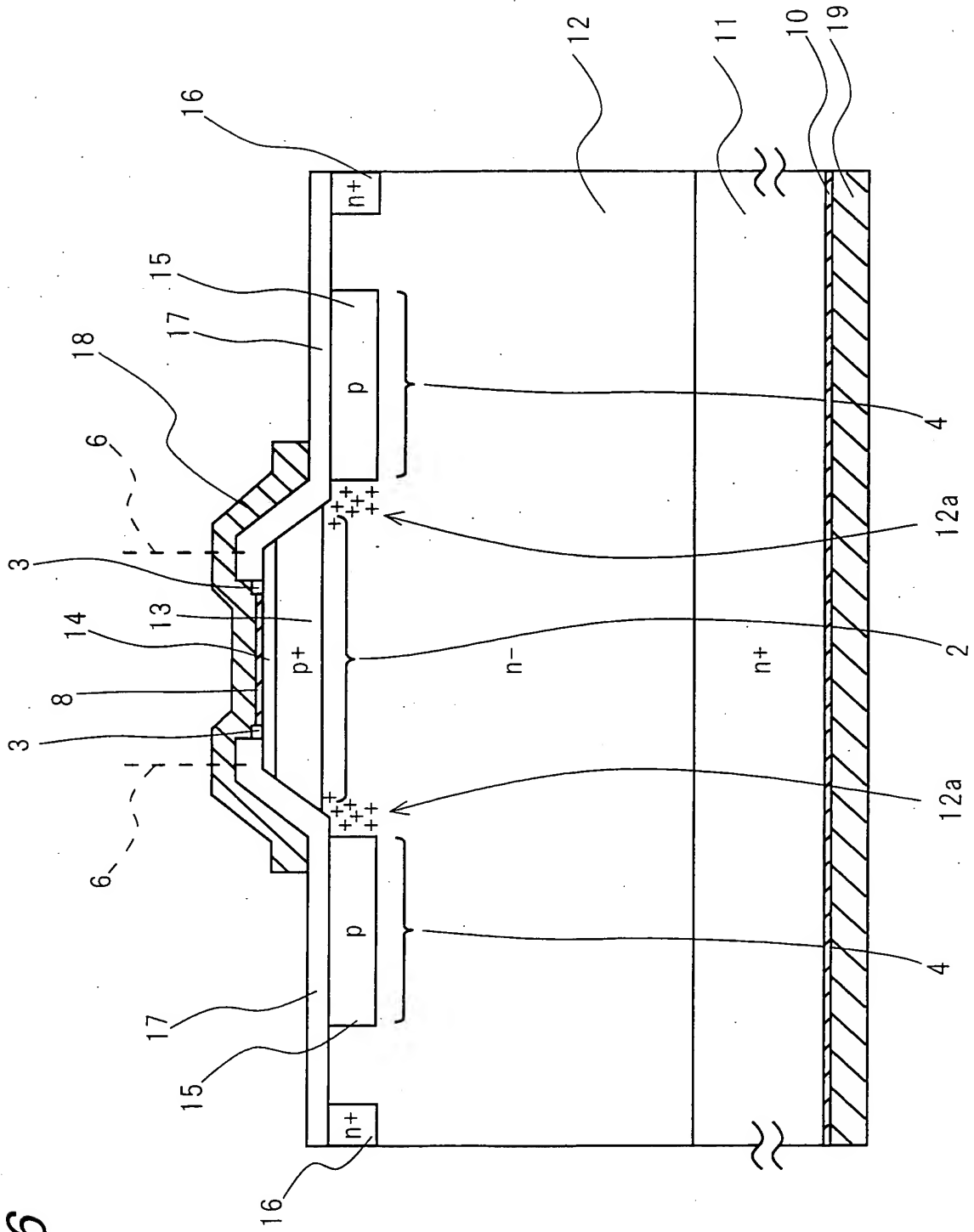


Fig. 7

